Attorney Docket No. 2110-047-03

In the specification:

Please replace paragraph 26 with the following paragraph:

[26] Then, during the second polymerizing etch, a second polymeric film ***33*** is formed, which grows at a rate that depends upon the etching voltage V_E. According to embodiments of the invention, the etching voltage V_E is varied during the second polymerizing etch so as to control the growth of the second polymeric film ***33*** and thus the slope of the walls ***35*** of the trench ***31***. In greater detail, the second polymerizing etch is performed in discrete steps and comprises a number N of steps performed in succession. As shown in **FIG. 17**, associated with the etching steps are respective durations T_1, T_2, ..., T_N and respective increasing values V_{E1}, V_{E2}, ..., V_{EN} of the etching voltage V_E. For example, the second polymerizing etch comprises three steps, each having a duration of 30 s. Furthermore, for each step the value of the etching voltage V_E is obtained by keeping the chamber voltage V_C constant (for example at 0 V) and imposing values of the wafer voltage V_W of 10 V, 20 V and 30 V, respectively. Thereby, a discrete-ramp etching voltage V_E is supplied. The etching steps are moreover performed one after the other, in rapid succession, substantially without interruptions.